

MAXIMUM RATINGS

Rating	Symbol	BC 177	BC 178	BC 179	Unit
Collector-Emitter Voltage	V _{CEO}	45	25	20	Vdc
Collector-Emitter Voltage	V _{CES}	50	30	25	Vdc
Collector-Base Voltage	V _{CBO}	50	30	25	Vdc
Emitter-Base Voltage	V _{EBO}	5			Vdc
Collector Current - Continuous	I _C	0.2			Amp
Total Device Dissipation @ T _A = 25°C Derate above 25°C	P _D	0.6		2.28	Watt mW/°C
Total Device Dissipation @ T _C = 25°C T _C = 100°C Derate above 25°C	P _D	1		6.67	Watt mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{Stg}	-65 to +200			°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	R _{θJC}	175	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector Emitter Leakage Current (V _{CE} = 20 V, I _E = 0) (V _{CE} = 20 V, I _E = 0, T _{Amb} = 125°C)	I _{CES}			100 4	nA μA
Collector Base Breakdown Voltage (I _C = 10 μA) BC177 BC178 BC179	V _{(BR)CBO}	50 30 25			V
Collector Emitter Breakdown Voltage (I _C = 2 mA, I _E = 0) BC177 BC178 BC179	V _{(BR)CEO}	45 25 20			V
Emitter Base Breakdown Voltage (I _E = 10 μA, I _C = 0)	V _{(BR)EBO}	5			V
ON CHARACTERISTICS					
DC Current Gain (I _C = 2 mA, V _{CE} = 5 V) BC177 BC178 BC179 V1 Group A Group B Group C Group	h _{FE}	120 120 180 70 120 180 380		460 800 800 140 220 460 800	
Collector Emitter Saturation Voltage (I _C = 10 mA, I _B = 0.5 mA) (I _C = 100 mA, I _B = 5 mA)	V _{CES(sat)}			0.2 0.6	V
Base Emitter Saturation Voltage (I _C = 10 mA, I _B = 0.5 mA) (I _C = 100 mA, I _B = 5 mA)	V _{BE(sat)}			0.7 0.9	0.8
Base Emitter on Voltage (I _C = 2 mA, V _{CE} = 5 V)	V _{BE(on)}	0.6		0.75	V
Collector Knee Voltage (I _C = 10 mA, I _B = the value for which (I _C = 11 mA, at V _{CE} = 1V)	V _{CES(K)}		0.4	0.6	V

DYNAMIC CHARACTERISTICS

Transition Frequency (V _{CE} = 5 V, I _C = 10 mA, f = 50 MHz)	f _T	200	300		MHz
Noise Figure (V _{CE} = 5 V, I _C = 0.2 mA, R _g = 2 kΩ) F = 30 Hz to 15 kHz F = 1 kHz, F = 200 Hz BC179 BC179 BC177/178	NF			4 4 10	dB

**BC177
BC178
BC179**

**CASE 22-03, STYLE 1
TO-18 (TO-206AA)**

TRANSISTOR

PNP SILICON

BC177, BC178, BC179
ELECTRICAL CHARACTERISTICS (continued) ($T_A = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
Output Capacitance ($V_{CB} = 10 \text{ V}$, $f = 1 \text{ MHz}$)	C _{obo}		3.5	4	nF
h_{21e} Parameters ($V_{CE} = 5 \text{ V}$, $I_C = 2 \text{ mA}$, $f = 1 \text{ kHz}$)	h_{21e}	125 125 240 75 125 240 450		500 900 900 150 260 500 900	
h_{11e} Parameters ($V_{CE} = 5 \text{ V}$, $I_C = 2 \text{ mA}$, $f = 1 \text{ kHz}$)	h_{11e}	1.0 1.6 3.2 6.0		2.2 4.5 8.5 15.0	k Ω
h_{22e} Parameters ($V_{GE} = 5 \text{ V}$, $I_C = 2 \text{ mA}$, $f = 1 \text{ kHz}$)	h_{22e}			25 30 60 110	μmhos